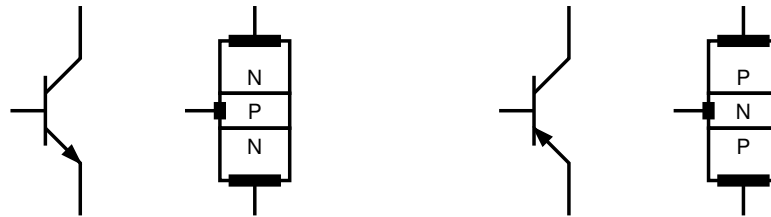# Overview of Technologies

Components for Logic
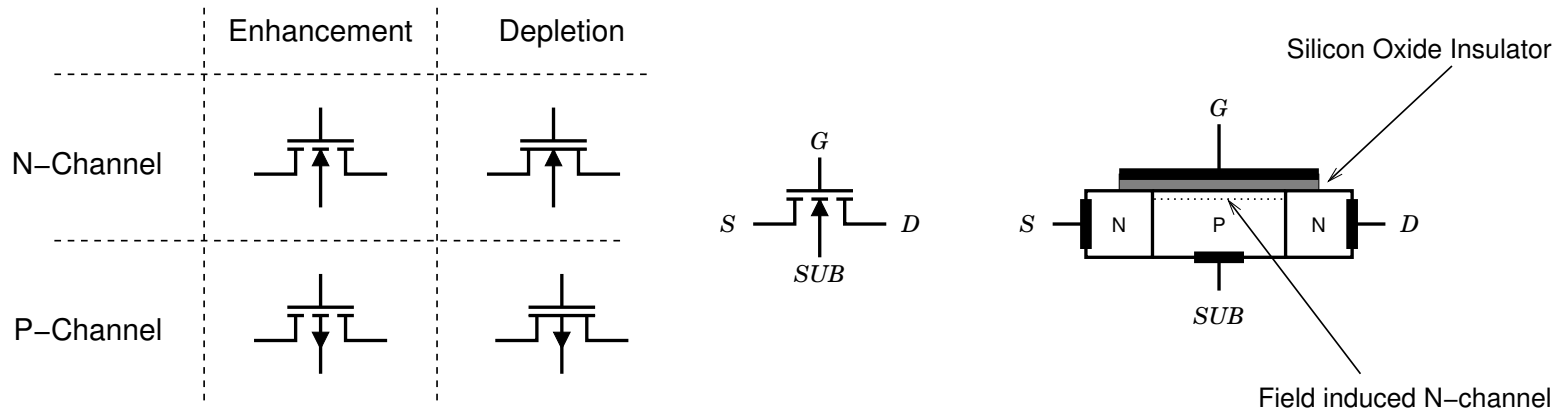
Diode

Bipolar Transistors
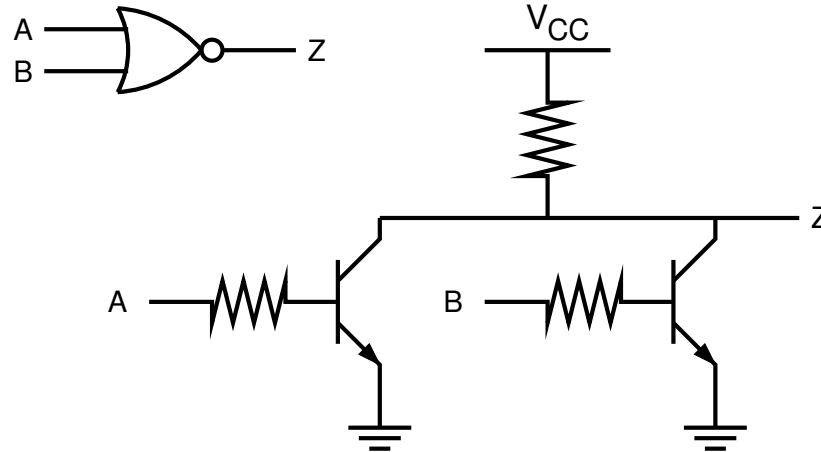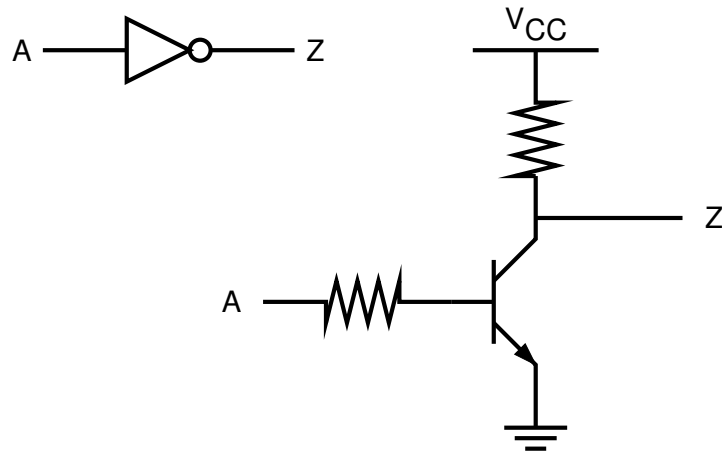
MOS Transistors

	Enhancement	Depletion
N–Channel		
P–Channel		

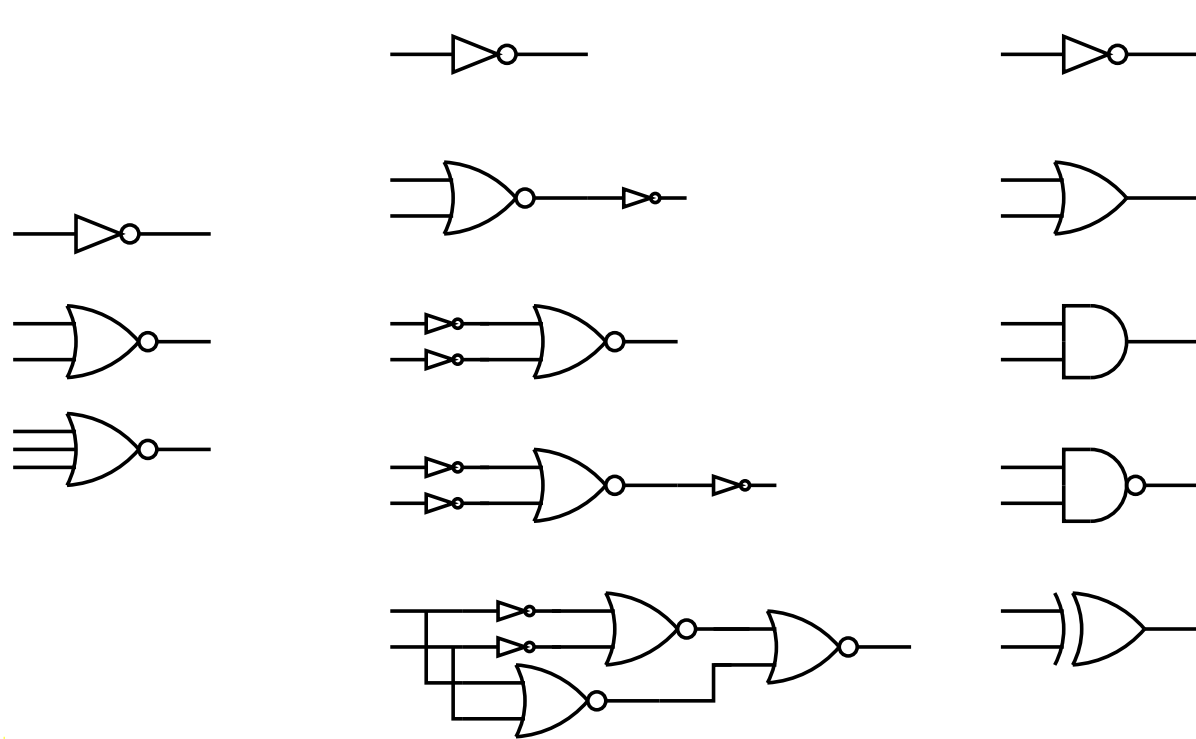Silicon Oxide Insulator

Field induced N–channel

2001

Overview of Technologies

RTL Inverter and NOR gate

Overview of Technologies

All functions can be realized using only the NOR gates[1] available in the RTL logic family.[2]
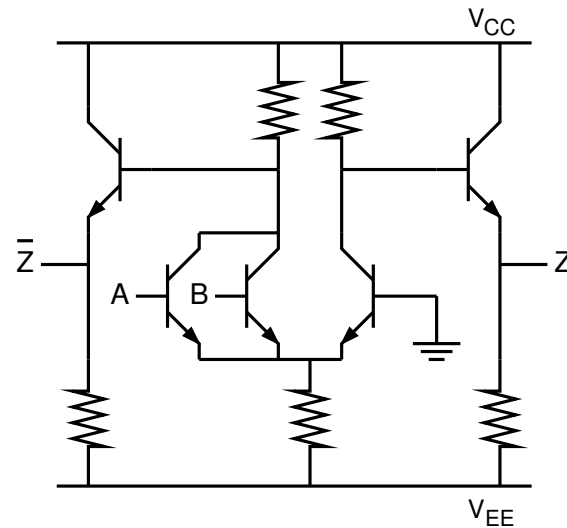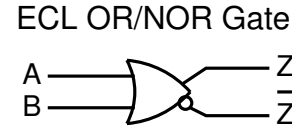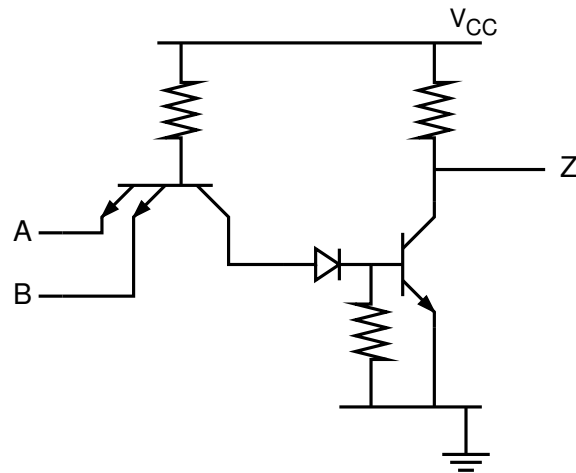
[1]Note that an inverter is a special case of a NOR gate with only one input.
[2]NAND gates could be used instead for logic families which support only NAND gates.

2003

Overview of Technologies

Other Bipolar Technologies

TTL NAND Gate

ECL OR/NOR Gate
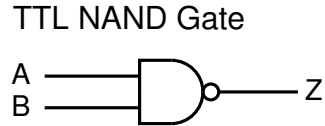
- TTL gives faster switching than RTL at the expense of greater complexity[3]. The characteristic multi-emitter transistor reduces the overall component count.

- ECL is a very high speed, high power, non-saturating technology.

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[3]Most TTL families are more complex than the basic version shown here

Overview of Technologies
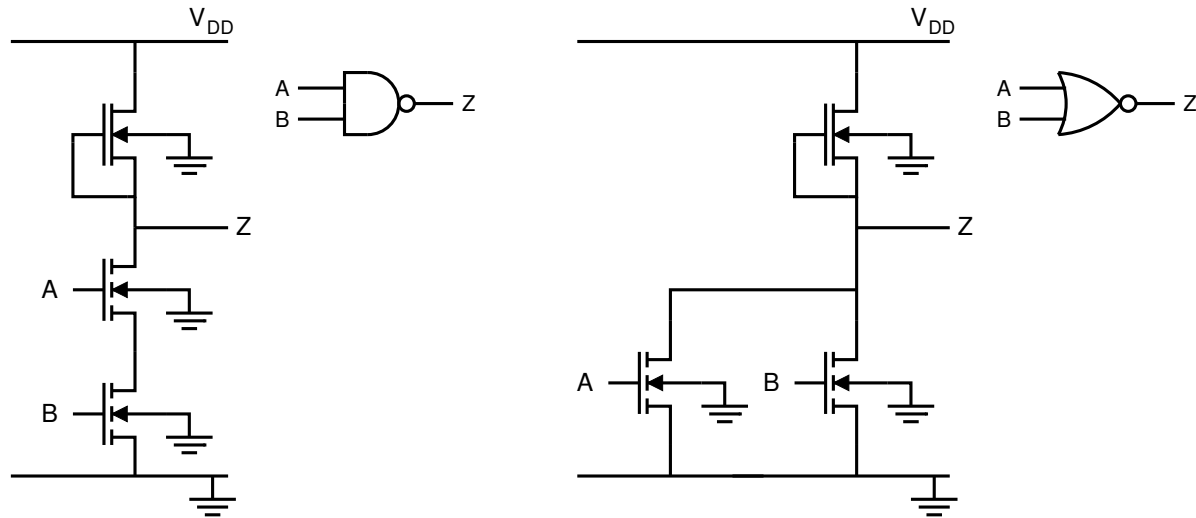
NMOS - a VLSI technology.

- Circuit function determined by series/parallel combination of devices.

- Depletion transistor acts as non-linear load resistor.

  Resistance increases as the enhancement device turns on, thus reducing power consumption.

- The low output voltage is determined by the size ratio of the devices.

2005

Overview of Technologies

Alternative transistors representations for NMOS circuits
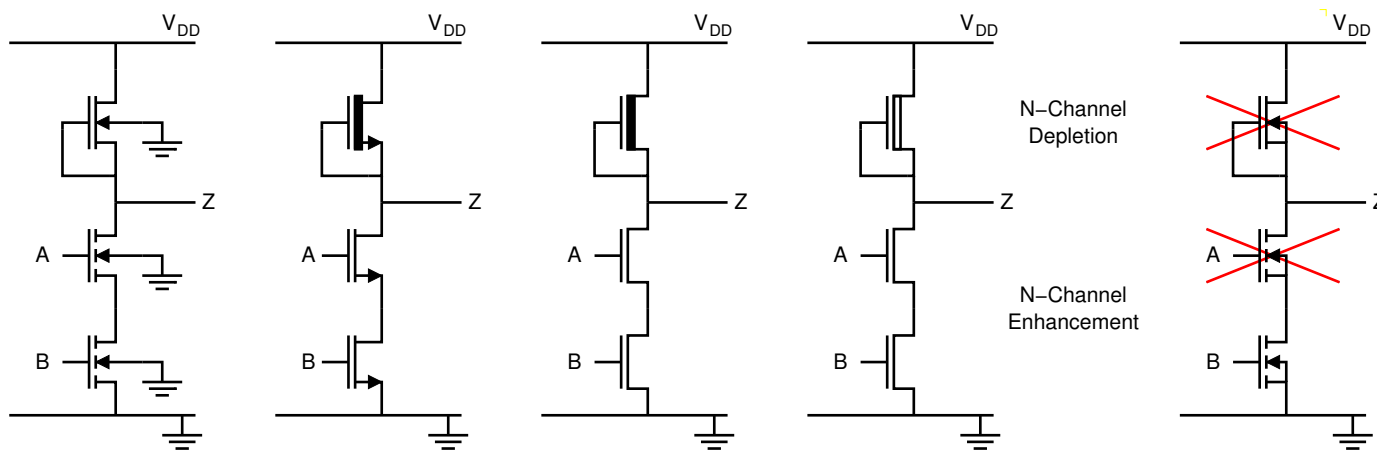
Various shorthands are used for simplifying NMOS circuit diagrams.

- Substrate connections need not be drawn since all must connect to Gnd.

- Since source and drain are indistinguishable in the layout, there is no need to show the source on the circuit diagram.

Note that schematic tools not designed for IC design will usually include inappropriate 3-terminal symbols.

2006
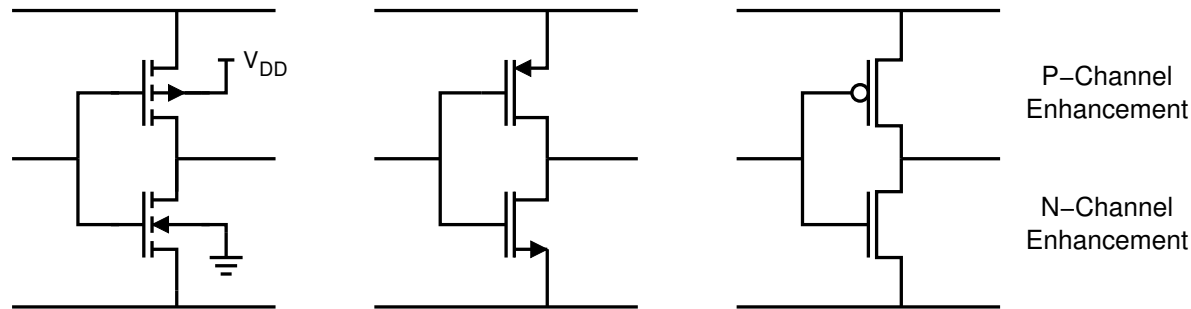
Overview of Technologies

CMOS logic

CMOS - *state of the art* VLSI.
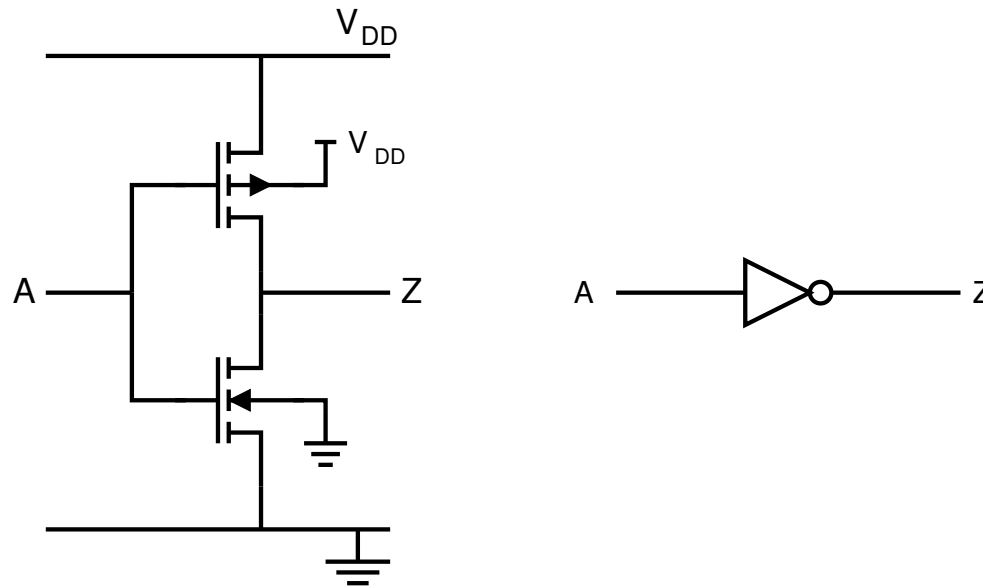
- An active PMOS device complements the NMOS device giving:

  - rail to rail output swing.
  - negligible static power consumption.

2007

Digital CMOS Circuits

Alternative transistor representations for CMOS circuits

V_{DD}

P–Channel
Enhancement

N–Channel
Enhancement

Digital CMOS circuits[4] tend to use simplified symbols like their NMOS counterparts.

- In general substrate connections are not drawn where they connect to Vdd (PMOS) and Gnd (NMOS).

- All CMOS devices are enhancement mode.

- Transistors act as simple digitally controlled switches.

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[4]in analog CMOS circuits we may have wells not connected to Vdd/GND
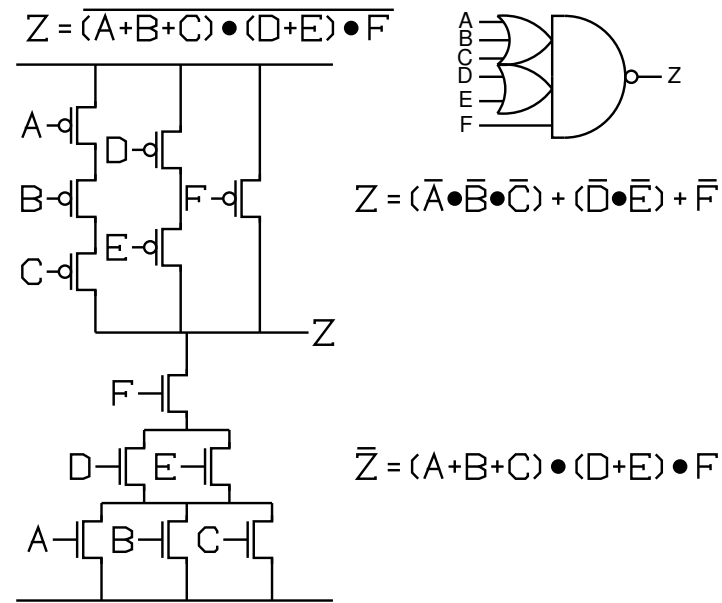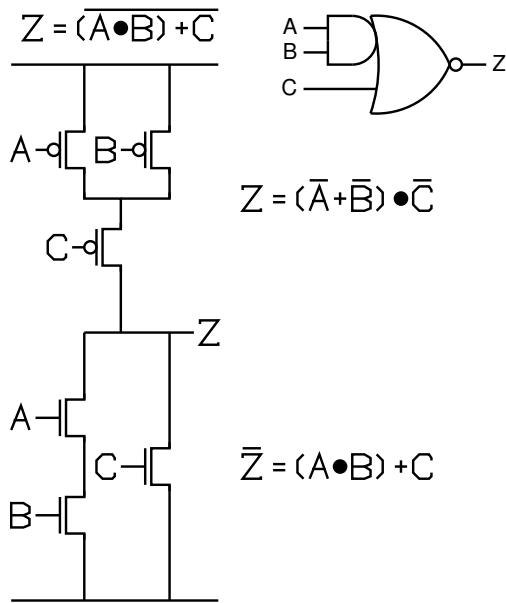
Digital CMOS Circuits

Static CMOS complementary gates

$$Z = \overline{A \bullet B}$$

$$Z = \overline{A \bullet B \bullet C}$$

$$Z = \overline{A + B + C}$$
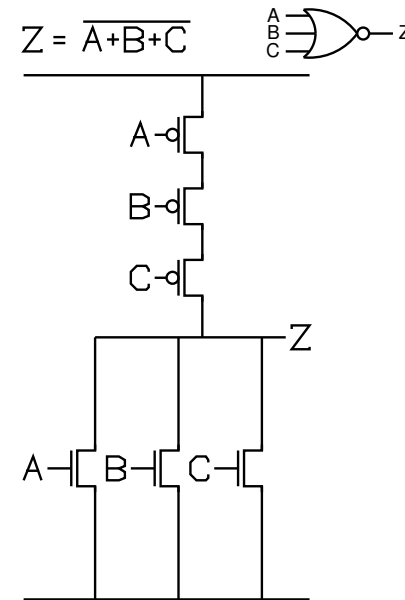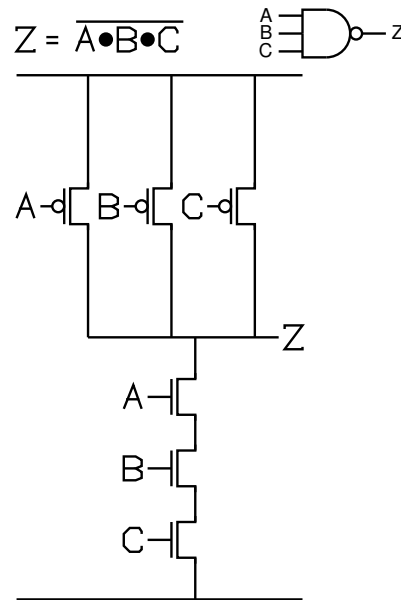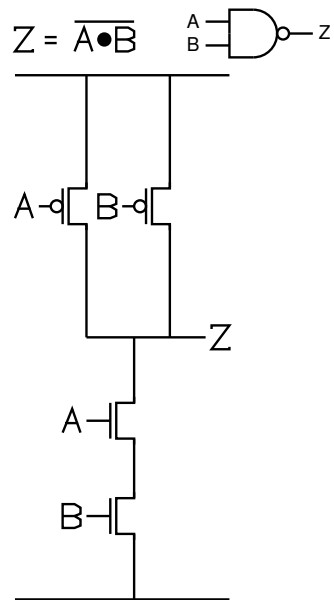
- For any set of inputs there will exist either a path to Vdd or a path to Gnd.

Digital CMOS Circuits

Compound Gates

$Z = \overline{(A \bullet B) + C}$

$Z = \overline{(\overline{A} + \overline{B}) \bullet \overline{C}}$

$\overline{Z} = (A \bullet B) + C$

$Z = \overline{(A + B + C) \bullet (D + E) \bullet F}$

$Z = \overline{(\overline{A} \bullet \overline{B} \bullet \overline{C}) + (\overline{D} \bullet \overline{E}) + \overline{F}}$

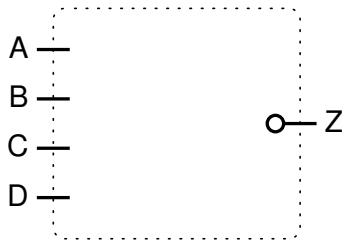$\overline{Z} = (A + B + C) \bullet (D + E) \bullet F$

- All compound gates are inverting.

- Realisable functions are arbitrary AND/OR expressions with inverted output.

2010

Digital CMOS Circuits

Compound Gate Example

$Z = \overline{(A \bullet B) + (C \bullet D)}$

Pull Up Network

$$Z = f(\overline{A}, \overline{B}, \overline{C}, \overline{D})$$

$$Z = \underline{\hspace{4cm}}$$

Symbol

A —
B —
C —
D —

○— Z

————————— V_{DD}

————————— Z

Pull Down Network

$$\overline{Z} = f(A, B, C, D)$$

$$\overline{Z} = (A \bullet B) + (C \bullet D)$$

————————— GND

2011